

LINEWIDTH SEMICONDUCTOR LASER, which in turn claimed benefit of prior U.S. Provisional Patent Application Serial No. 60/004,620, filed 09/29/95 by Parviz Tayebati for AGILE, WIDELY TUNABLE DIODE LASER WITH NARROW LINEWIDTH, and prior U.S. Provisional Patent Application Serial No. 60/004,940, filed 10/04/95 by Parviz Tayebati for WIDELY TUNABLE, MINIATURE SINGLE MODE DIODE LASER ARRAYS WITH NARROW LINEWIDTH.--

Remarks

As noted in the accompanying REQUEST FOR FILING RULE 1.53(B) CONTINUATION APPLICATION, this is a continuation of pending prior application Serial No. 09/532,529, filed 03/21/00 by Parviz Tayebati for ELECTRO-OPTICALLY TUNABLE EXTERNAL CAVITY MIRROR FOR A NARROW LINEWIDTH SEMICONDUCTOR LASER, which is in turn a continuation application of prior application Serial No. 08/726,049, filed 10/6/98 by Parviz Tayebati for ELECTRO-OPTICALLY TUNABLE EXTERNAL CAVITY MIRROR FOR A NARROW LINEWIDTH SEMICONDUCTOR LASER, which is in turn a Continued Prosecution Application (CPA) of prior application Serial No. 08/726,049, filed 09/27/96 by Parviz Tayebati for ELECTRO-OPTICALLY TUNABLE EXTERNAL CAVITY MIRROR FOR A NARROW LINEWIDTH SEMICONDUCTOR LASER, which in turn claimed benefit of prior U.S. Provisional Patent Application Serial No. 60/004,620, filed 09/29/95 by Parviz Tayebati for AGILE, WIDELY TUNABLE DIODE LASER WITH NARROW LINEWIDTH, and prior U.S. Provisional Patent Application Serial No. 60/004,940, filed 10/04/95 by Parviz Tayebati for WIDELY TUNABLE, MINIATURE SINGLE MODE DIODE LASER ARRAYS WITH NARROW LINEWIDTH. The above amendment is intended to make this fact of record in the specification of this continuation application.

Respectfully submitted,

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